

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ\text{C}$
20V	90m $\Omega$ @ $V_{GS} = 4.5\text{V}$	2.8A
	120m $\Omega$ @ $V_{GS} = 2.5\text{V}$	2.4A

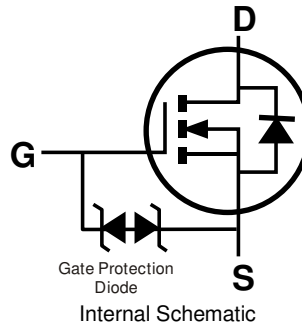
## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

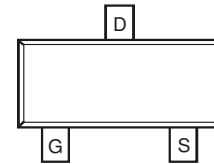
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control



Top View



Internal Schematic



Top View

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

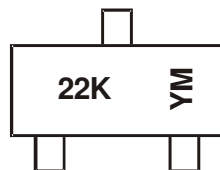
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (Ⓔ)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2302UK-7	SOT23	3,000/Tape & Reel
DMG2302UK-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



22K = Product Type Marking Code  
 YM = Date Code Marking  
 Y or Y= Year (ex: C = 2015)  
 M = Month (ex: 9 = September)

### Date Code Key

Year Code	2015	2016	2017	2018	2019	2020	2021	2022
Code	C	D	E	F	G	H	I	J

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	20	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	2.8	A
		$T_A = +70^\circ\text{C}$	2.2	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	1.1	A	
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{DM}$	12	A	

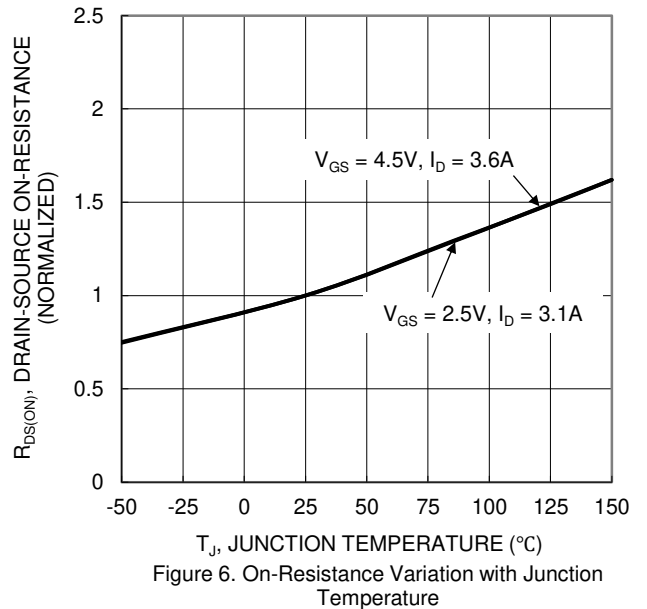
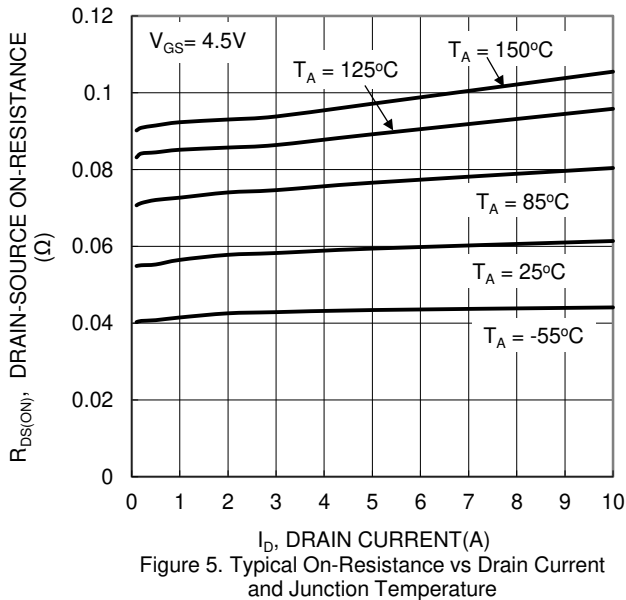
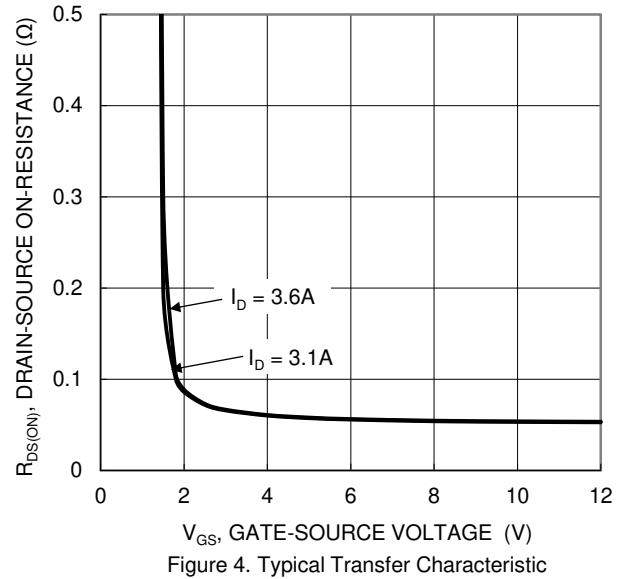
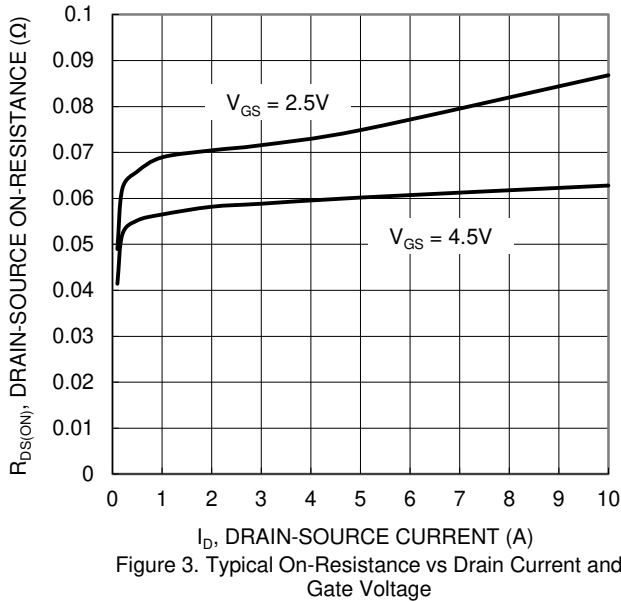
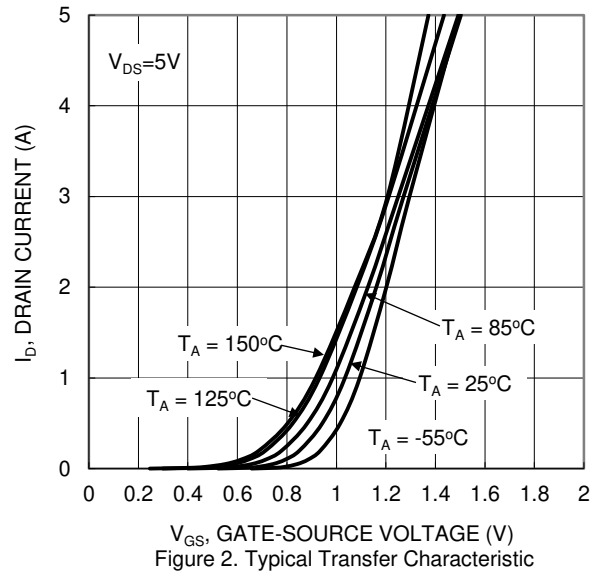
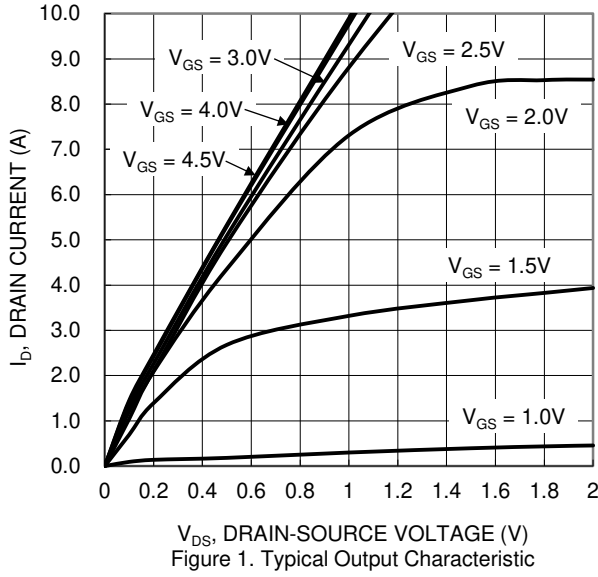
**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_D$	0.66	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State $R_{\theta JA}$	192	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	$P_D$	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State $R_{\theta JA}$	115	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	10	$\mu\text{A}$	$T_J = +25^\circ\text{C}, V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.3	0.6	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	61	90	m $\Omega$	$V_{GS} = 4.5\text{V}, I_D = 3.6\text{A}$
			80	120		$V_{GS} = 2.5\text{V}, I_D = 3.1\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1.0\text{A}$
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	$C_{ISS}$	—	130	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	26	—	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	18	—	pF	
Gate Resistance	$R_G$	—	2.7	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_G$	—	1.4	—	nC	$V_{DS} = 10\text{V}, I_D = 3.6\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_G$	—	2.8	—	nC	
Gate-Source Charge	$Q_{GS}$	—	0.1	—	nC	
Gate-Drain Charge	$Q_{GD}$	—	0.5	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	0.6	—	ns	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V},$ $R_G = 1\Omega, R_L = 2.78\Omega$
Turn-On Rise Time	$t_R$	—	2.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	4.2	—	ns	
Turn-Off Fall Time	$t_F$	—	1.7	—	ns	
Reverse Recovery Time	$t_{RR}$	—	5.3	—	ns	$I_F = 3.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{RR}$	—	0.5	—	nC	$I_F = 3.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



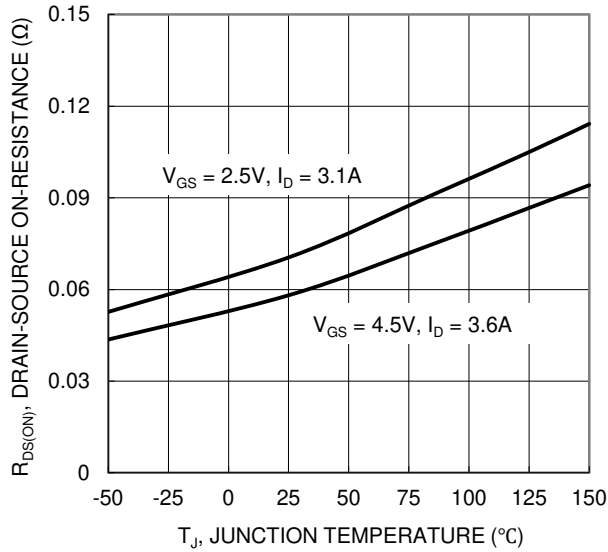


Figure 7. On-Resistance Variation with Junction Temperature

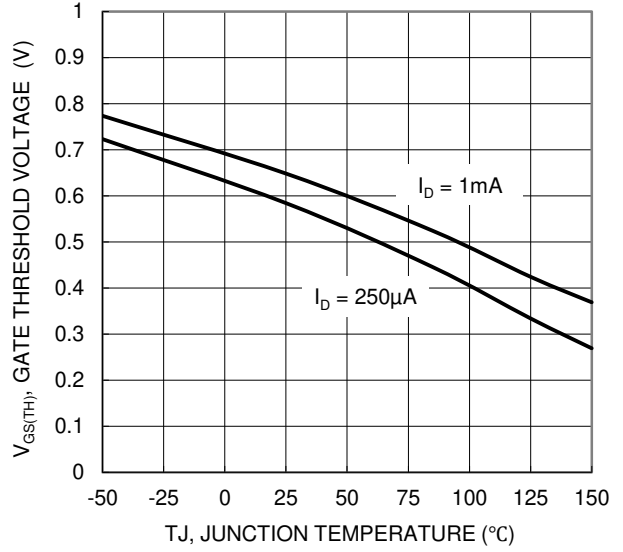


Figure 8. Gate Threshold Variation vs Junction Temperature

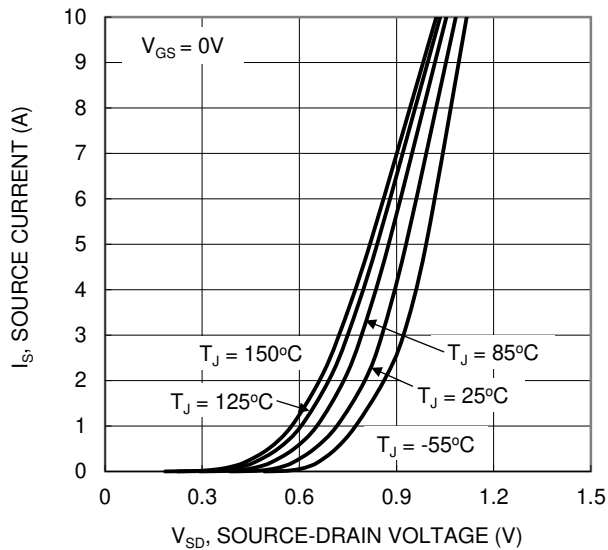


Figure 9. Diode Forward Voltage vs. Current

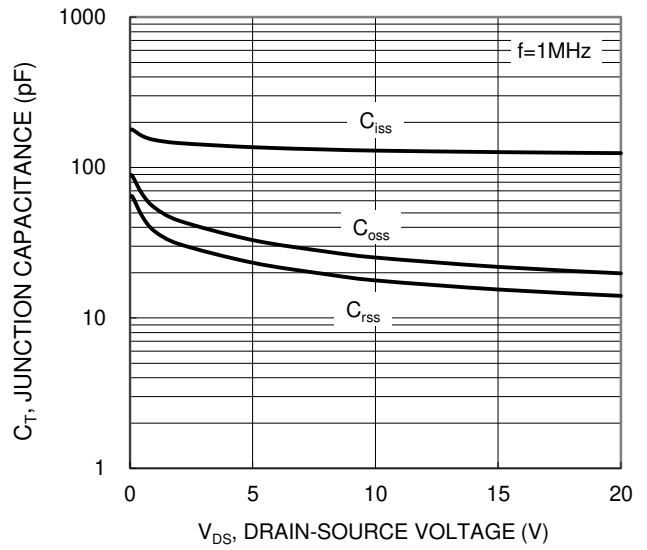


Figure 10. Typical Junction Capacitance

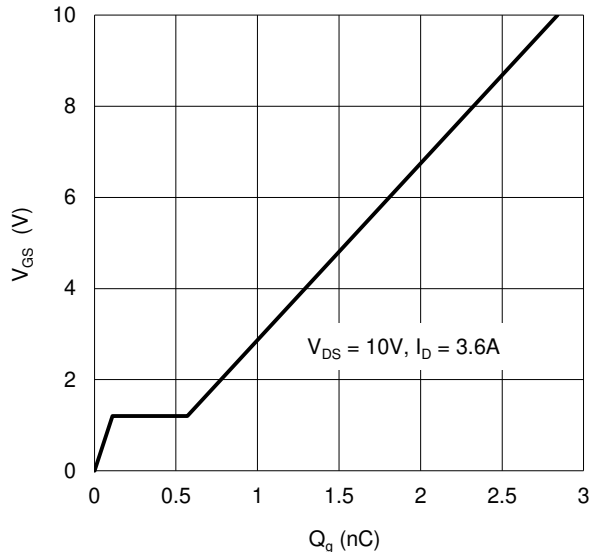


Figure 11. Gate Charge

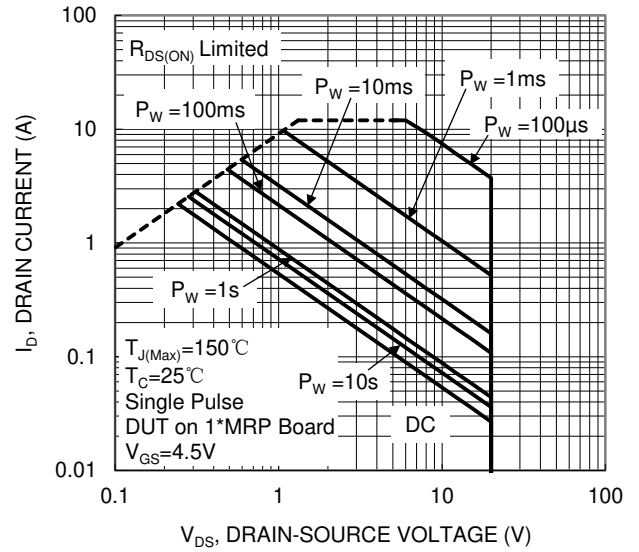
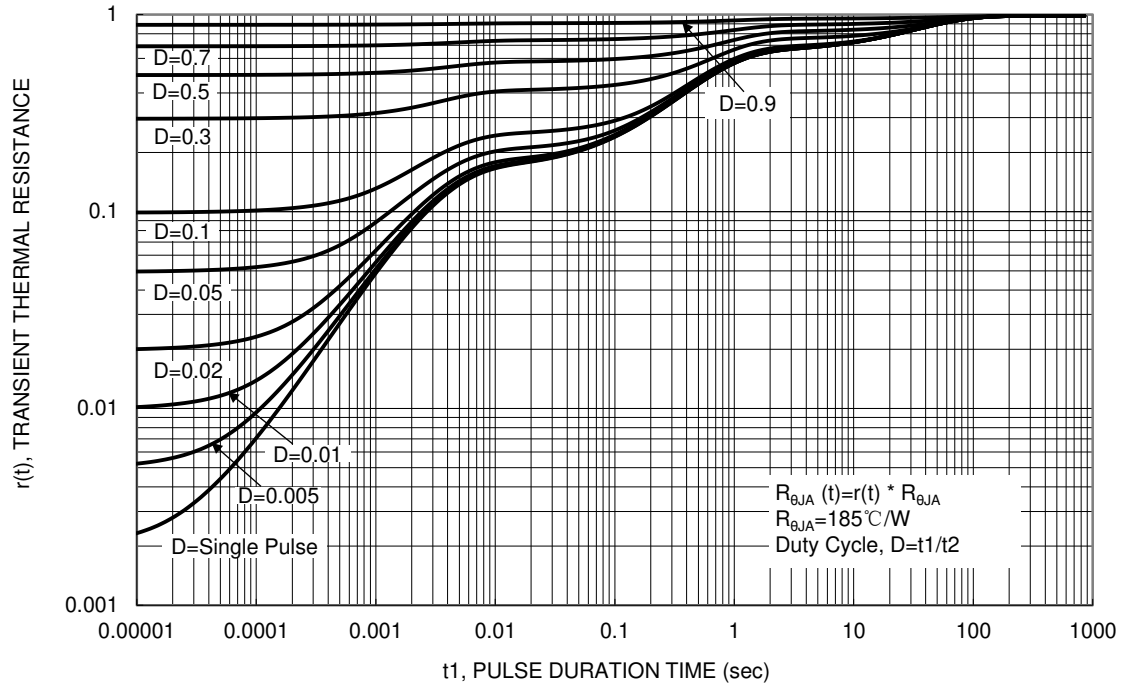


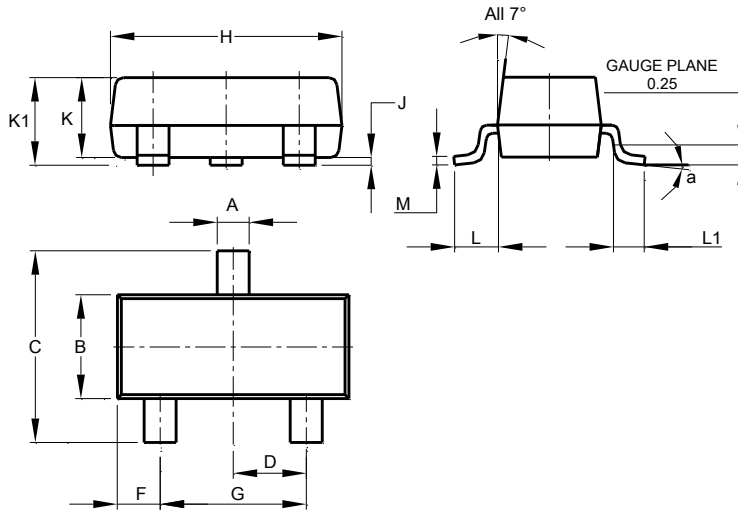
Figure 12. SOA, Safe Operation Area



**Package Outline Dimensions**

Please see AP02001 at [http://www.diodes.com/\\_files/datasheets/ap02001.pdf](http://www.diodes.com/_files/datasheets/ap02001.pdf) for the latest version.

**SOT23**

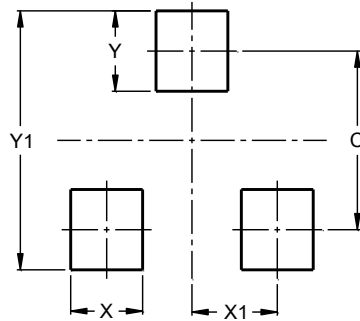


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at [http://www.diodes.com/\\_files/datasheets/ap02001.pdf](http://www.diodes.com/_files/datasheets/ap02001.pdf) for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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